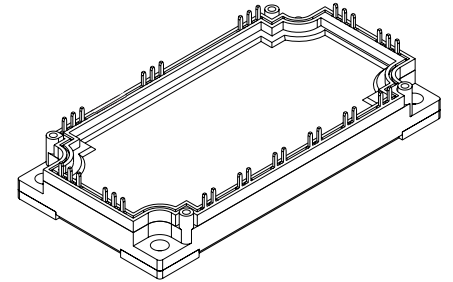
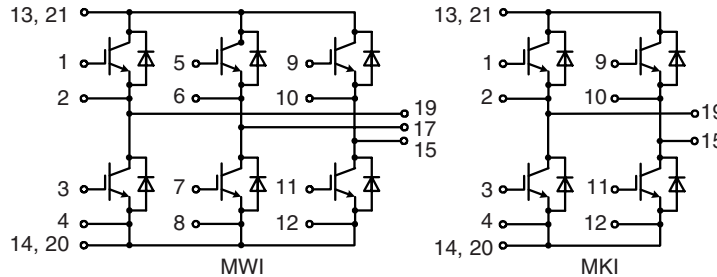


IGBT Modules

Sixpack, H Bridge

Short Circuit SOA Capability
 Square RBSOA

$I_{C25} = 165 \text{ A}$
 $V_{CES} = 1200 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 2.0 \text{ V}$



IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^\circ\text{C}$	165	A
I_{C80}	$T_C = 80^\circ\text{C}$	115	A
I_{CM}	$V_{GE} = \pm 15 \text{ V}; R_G = 12 \Omega; T_{VJ} = 125^\circ\text{C}$	200	A
V_{CEK}	RBSOA; clamped inductive load; $L = 100 \mu\text{H}$	V_{CES}	
t_{SC}	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 12 \Omega; T_{VJ} = 125^\circ\text{C}$ SCSOA; non-repetitive	10	μs
P_{tot}	$T_C = 25^\circ\text{C}$	640	W

Features

- NPT³ IGBTs
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance also in resonant circuits
- HiPerFRED™ diode:
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated copper base plate

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 100 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.0 2.3	V V	
$V_{GE(th)}$	$I_C = 4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.4	1.4 mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			400 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 100 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 12 \Omega$		330	ns	
E_{on}			15	ns	
E_{off}			750	ns	
				45	ns
				12	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		7.4	nF	
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 150 \text{ A}$		0.76	μC	
R_{thJC}	(per IGBT)			0.19 K/W	

Typical Applications

- MWI
 - AC drives
 - power supplies with power factor correction
- MKI
 - motor control
 - . DC motor amature winding
 - . DC motor excitation winding
 - . synchronous motor excitation winding
 - supply of transformer primary winding
 - . power supplies
 - . welding
 - . X-ray
 - . battery charger

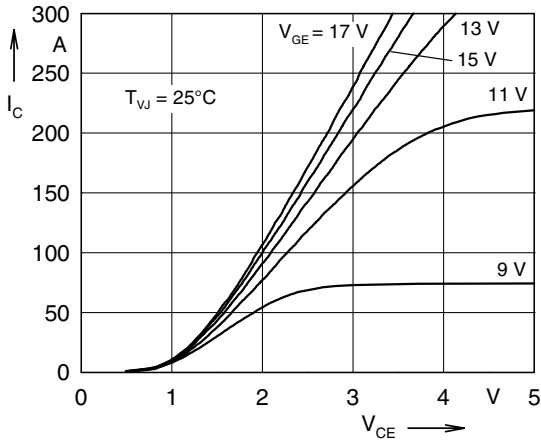


Fig. 1 Typ. output characteristics

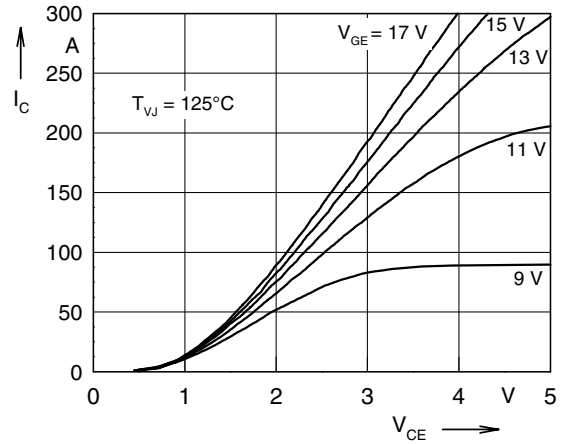


Fig. 2 Typ. output characteristics

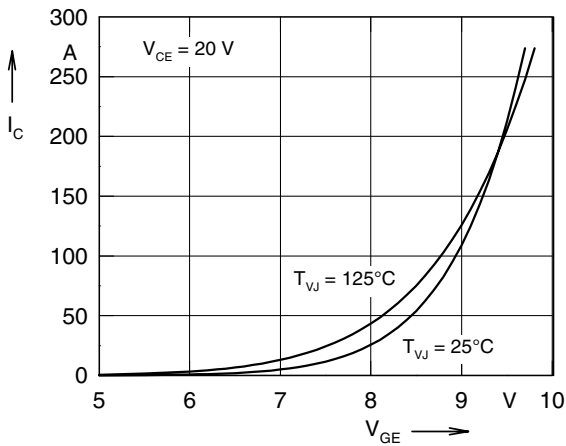


Fig. 3 Typ. transfer characteristics

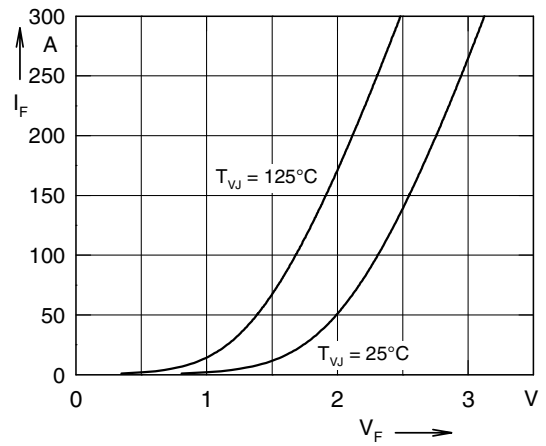


Fig. 4 Typ. forward characteristics of free wheeling diode

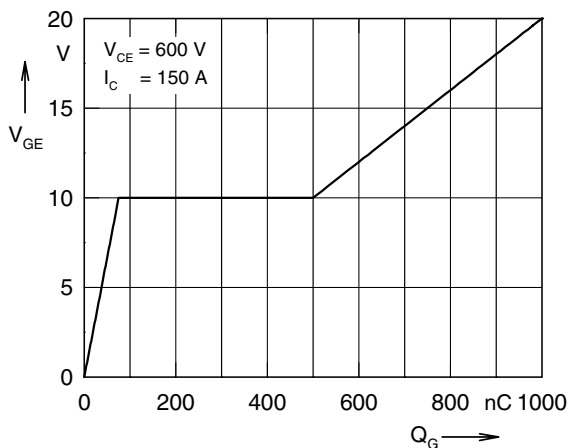


Fig. 5 Typ. turn on gate charge

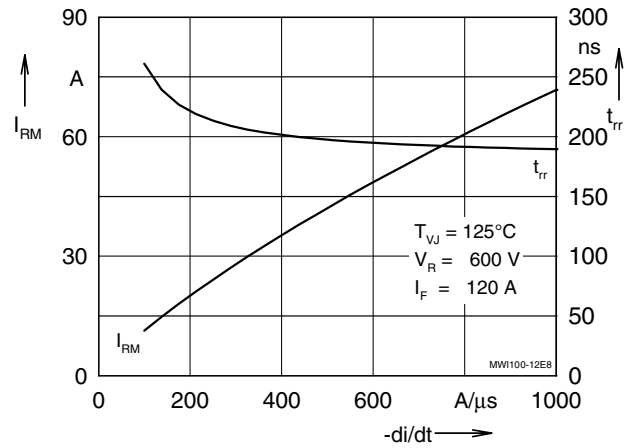


Fig. 6 Typ. turn off characteristics of free wheeling diode

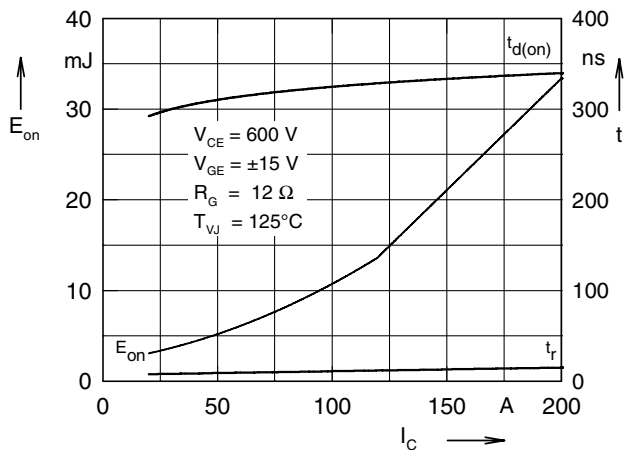


Fig. 7 Typ. turn on energy and switching times versus collector current

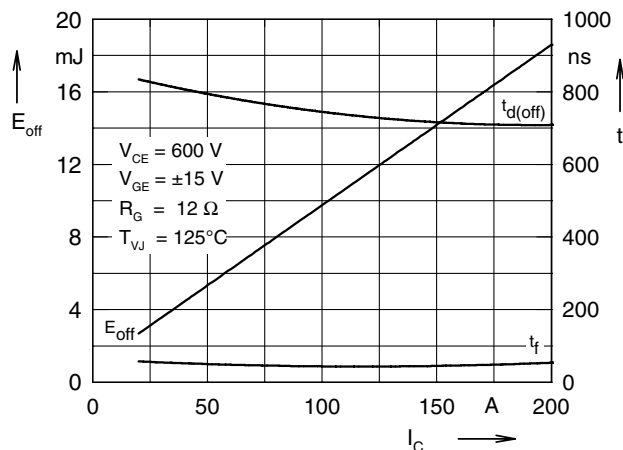


Fig. 8 Typ. turn off energy and switching times versus collector current

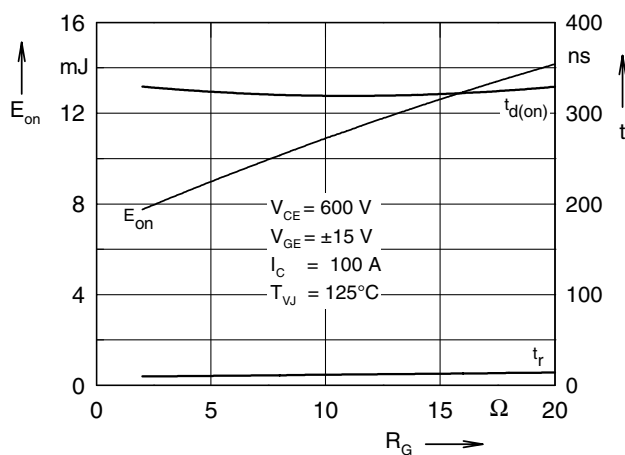


Fig. 9 Typ. turn on energy and switching times versus gate resistor

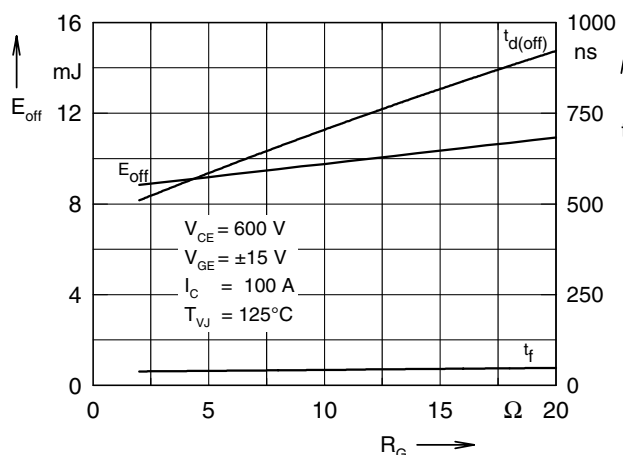


Fig. 10 Typ. turn off energy and switching times versus gate resistor

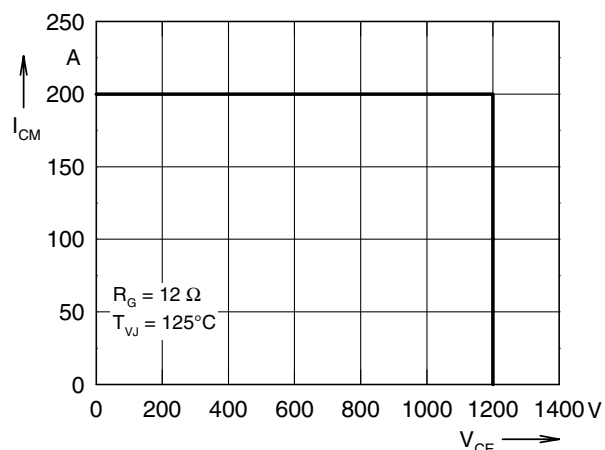


Fig. 11 Reverse biased safe operating area RBSOA

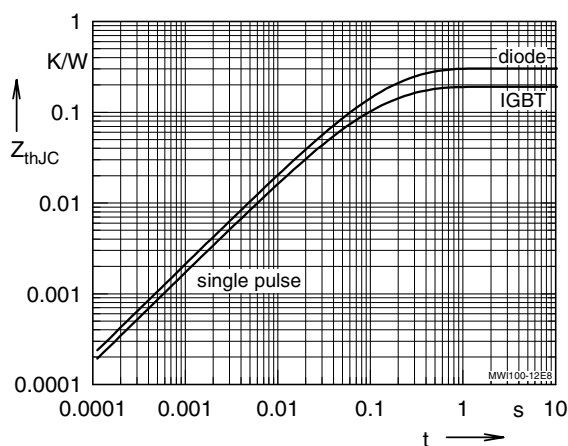


Fig. 12 Typ. transient thermal impedance